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ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes: a first cladding layer, which is made of a nitride semiconductor of a first conductivity type and is formed over a substrate; an active 5 layer, which is made of another nitride semiconductor and is formed over the first cladding layer; and a second cladding layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer. A spontaneous-emission-absorbing layer, which is made 10 of yet another nitride semiconductor of the first conductivity type and has such an energy gap as absorbing spontaneous emission that has been radiated from the active layer, is formed between the substrate and the first cladding layer.

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